# NPN-Si-Fototransistor mit $V_{\lambda}$ Charakteristik Silicon NPN Phototransistor with $V_{\lambda}$ Characteristics

# **SFH 3410**



### **Wesentliche Merkmale**

- Speziell geeignet f
  ür Anwendungen im Bereich von 350 nm bis 970 nm
- Angepaßt an die Augenempfindlichkeit  $(V_{\lambda})$
- SMT-Bauform ohne Basisanschluß, geeignet für Vapor Phase-Löten und IR-Reflow-Löten (JEDEC level 4)
- Nur gegurtet lieferbar

### Anwendungen

- Umgebungslicht-Detektor
- Beleuchtungsmesser
- Dimmungssensor für Hintergrundbeleuchtung
- "Messen/Steuern/Regeln"

**Opto Semiconductors** 

#### **Features**

- Especially suitable for applications from 350 nm to 970 nm
- Adapted to human eye sensitivity  $(V_{\lambda})$
- SMT package without base connection, suitable for vapor phase and IR reflow soldering (JEDEC level 4)
- · Only available on tape and reel

# **Applications**

- Ambient light detector
- · Exposure meter for daylight and artificial light
- · Sensor for Backlight-Dimming
- For control and drive circuits

tSilicon NPN Phototransistor with  $V_{\lambda}$  Characterist

Typ Type	Bestellnummer Ordering Code	Fotostrom $E_{\rm v}$ = 20 lx, Standard light A, $V_{\rm CE}$ = 5 V Photocurrent lpce ( $\mu$ A)
SFH 3410	Q62702-P5160	>3.2
SFH 3410 -1/2	Q65110A0049	3.210
SFH 3410 -2/3	Q65110A0050	516
SFH 3410 -3/4	Q65110A0051	825



# **Grenzwerte** ( $T_A = 25$ °C) **Maximum Ratings**

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	$T_{ m op}$ ; $T_{ m stg}$	- 40 <b>+</b> 100	°C
Kollektor-Emitterspannung Collector-emitter voltage	$V_{\sf CE}$	5.5	V
Kollektorstrom Collector current	$I_{C}$	20	mA
Emitter-Kollektorspannung Emitter-collector voltage	$V_{EC}$	0.5	V

# Kennwerte ( $T_A$ = 25 °C) Characteristics

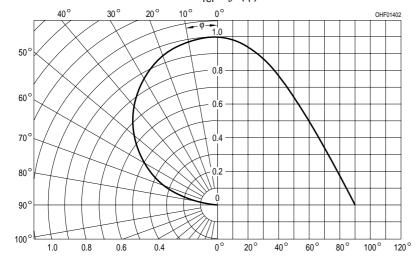
Bezeichnung Parameter	Symbol Wert Value		Einheit Unit	
Wellenlänge der max. Fotoempfindlichkeit Wavelength of max. sensitivity	$\lambda_{Smax}$	570	nm	
Spektraler Bereich der Fotoempfindlichkeit $S=10\%$ von $S_{\rm max}$ Spectral range of sensitivity $S=10\%$ of $S_{\rm max}$	λ	350 970	nm	
Bestrahlungsempfindliche Fläche Radiant sensitive area	A	0.29	mm <sup>2</sup>	
Abmessung der Chipfläche Dimensions of chip area	$L \times B$ $L \times W$	0.75 × 0.75	mm × mm	
Halbwinkel Half angle	φ	± 60	Grad. deg.	
Kapazität, $V_{\rm CE}$ = 0 V, $f$ = 1 MHz, $E$ = 0 Capacitance	$C_{CE}$	16	pF	
Dunkelstrom Dark current $V_{\rm R} = 5 \text{ V}$	$I_{\sf CEO}$	3 (< 50)	nA	
Fotostrom Photocurrent $E_{\rm v}$ = 20 lx, Normlicht/standard light A, $V_{\rm CE}$ = 5 V	$I_{PCE}$	>3.2	μΑ	



Bezeichnung Parameter	Symbol Symbol	Wert Value				Einheit Unit
		-1	-2	-3	-4	
Fotostrom Photocurrent $E_{\rm v}$ = 20 lx, Normlicht/standard light A $V_{\rm CE}$ = 5 V	$I_{\sf PCE}$	3.26.3	510	816	12.525	μΑ
Kollektor-Emitter-Sättigungsspannung Collector-emitter saturation voltage $I_{\rm C} = I_{\rm PCEmin}^{-1} \times 0.3, E_{\rm V} = 20 \ \rm lx$	$V_{CEsat}$	100	100	100	100	mV

 $I_{
m PCEmin}$  ist der minimale Fotostrom der jeweiligen Gruppe

# Directional Characteristics $S_{\text{rel}} = f(\phi)$

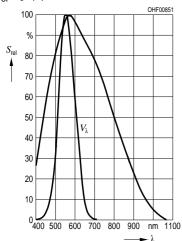




 $<sup>^{\</sup>rm 1)}~~I_{\rm PCEmin}$  is the min. photocurrent of the specified group

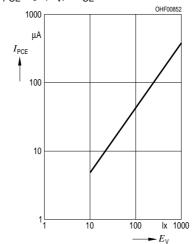
# Relative Spectral Sensitivity





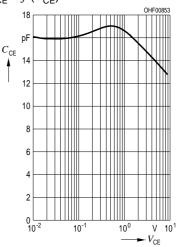
### **Photocurrent**

$$I_{\mathrm{PCE}} = f\left(E_{\mathrm{V}}\right)\!,\; V_{\mathrm{CE}} = 5\;\mathrm{V}$$



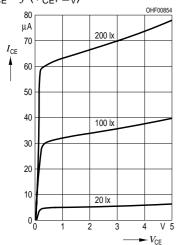
## **Collector-Emitter Capacitance**

$$C_{\mathsf{CE}} = f(V_{\mathsf{CE}})$$

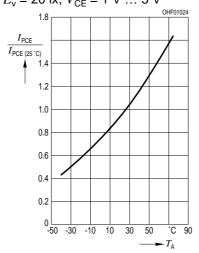


### **Collector-Emitter Current**

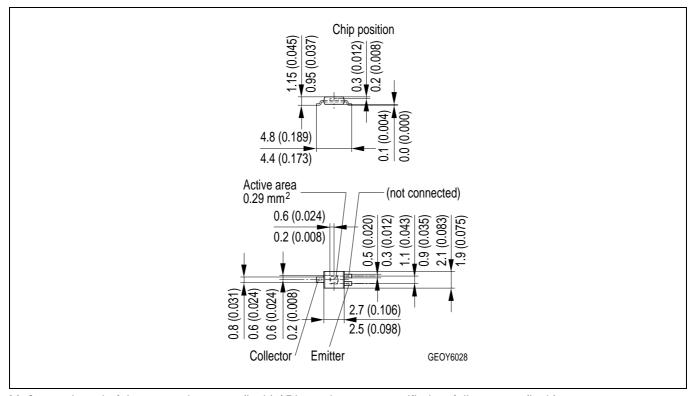
$$I_{CE} = f(V_{CE}; E_{V})$$



# $\begin{array}{l} \textbf{Photocurrent} \; I_{\text{PCE}}/I_{\text{PCE}(25 \, ^{\circ}\text{C})} = f \; (T_{\text{A}}) \\ E_{\text{v}} = 20 \; \text{lx}, \; V_{\text{CE}} = 1 \; \text{V} \; \dots \; 5 \; \text{V} \end{array}$



# Maßzeichnung Package Outlines



Maße werden wie folgt angegeben: mm (inch) / Dimensions are specified as follows: mm (inch).

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#### **Packing**

Please use the recycling operators known to you. We can also help you – get in touch with your nearest sales office. By agreement we will take packing material back, if it is sorted. You must bear the costs of transport. For packing material that is returned to us unsorted or which we are not obliged to accept, we shall have to invoice you for any costs incurred.

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